#### Lecture 9 Outline

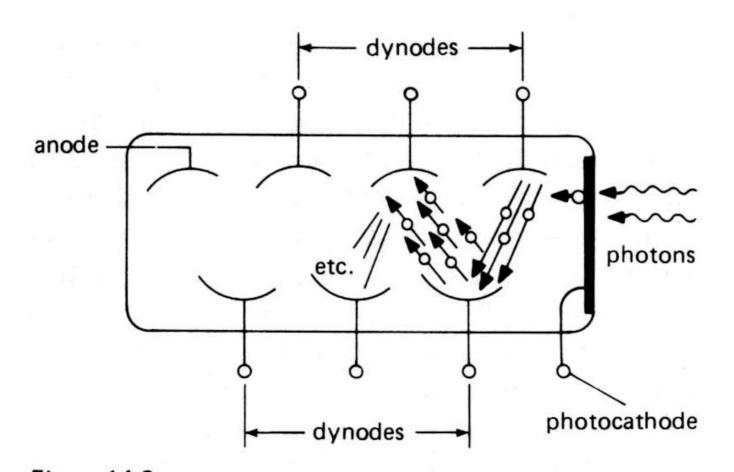
- Role of detectors
- Photomultiplier tubes (photoemission)
- Modulation transfer function
- Photoconductive detector physics
- Detector architecture

#### Where detectors are used in science & technology

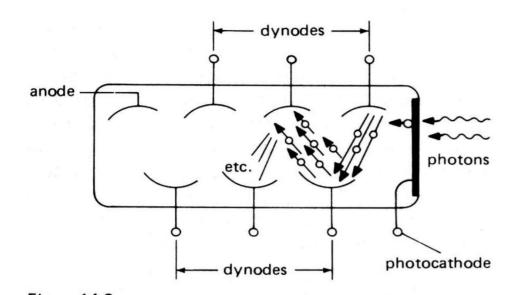
Scientific: Imaging
Spectroscopy

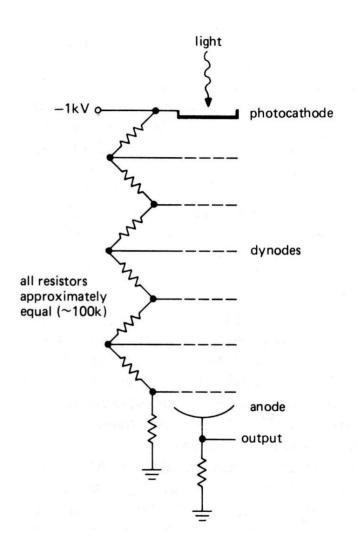
## Photomultiplier tube

Electron multiplier



## Photomultiplier tube

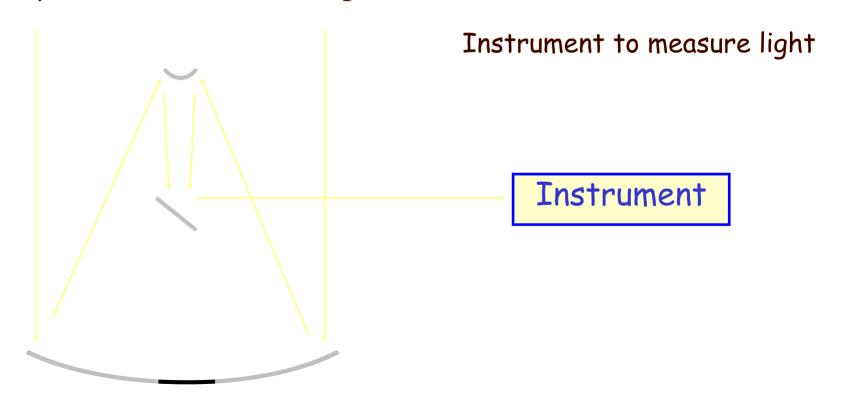




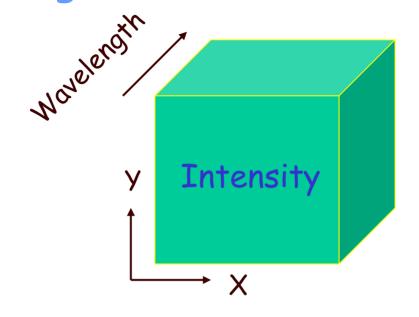
## Optical and Infrared Astronomy (0.3 to 25 μm)

#### Two basic parts

Telescope to collect and focus light



#### Instrument goal is to measure a 3-D data cube

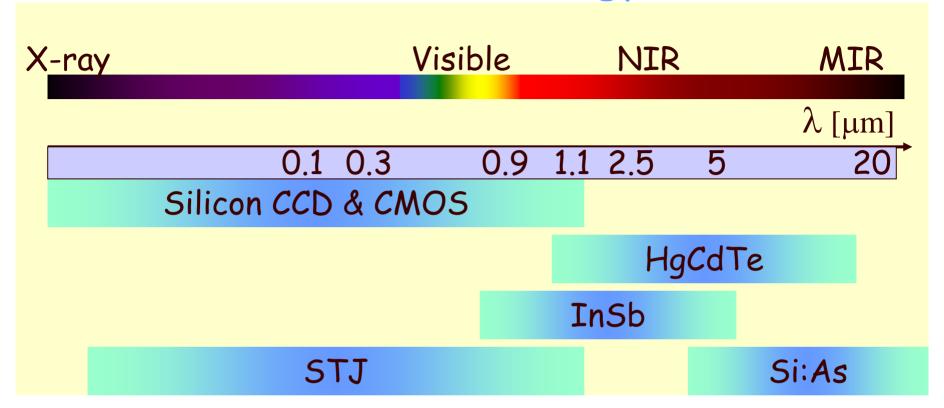


But array detectors are 2-dimensional!

- Our detectors are BLACK & WHITE
- Cannot measure color, only intensity

So the optics of the instrument are used to map a portion of the 3-D data cube on to the 2-D detector

#### Detector zoology



#### We will concentrate on

- Optical silicon-based (CCD, CMOS)
- Infrared IR material plus silicon CMOS multiplexer

#### The Ideal Detector

Detect 100% of photons

- ✓ Up to 99% quantum efficiency
- Each photon detected as a delta function
- ✓ One electron for each photon

Large number of pixels

✓ 1 billion pixels by 2008

- Time tag for each photon
- No framing detectors
- Measure photon wavelength
- No defined by filter (except STJs)
- Measure photon polarization
- No defined by filter

#### Plus READOUT NOISE and other "features"

# Sensitvity

## 5 basic steps of optical/IR photon detection

- 1. Get light into the detector Anti-reflection coatings
- 2. Charge generation
  Popular materials: Silicon, HgCdTe, InSb
- 3. Charge collection

Electrical fields within the material collect photoelectrons into pixels.

4. Charge transfer

If CMOS, no charge transfer required. For CCD, move photoelectrons to the edge where amplifiers are located.

5. Charge amplification & digitization

Amplification process is noisy. In general CCDs have lowest noise, CMOS detectors have higher noise.

Quantum Efficiency

Point
Spread
Function

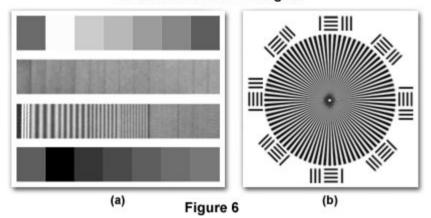
## Step 1: Get light into the detector

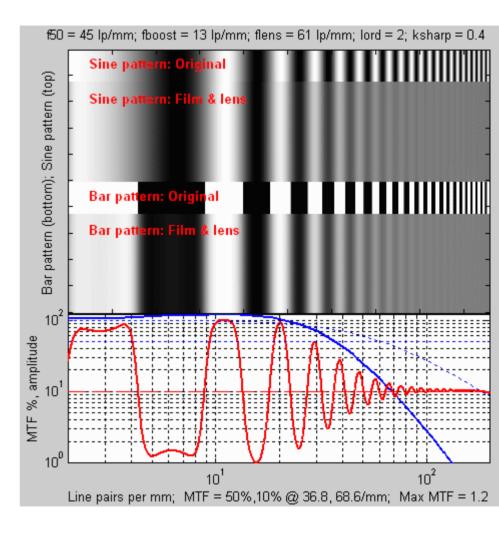
Good optics
No lost light
No stray light
Anti-reflection coatings

Anti-reflection coatings will be discussed in next lecture.

#### Modulation Transfer Function

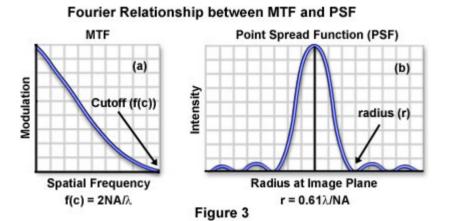
#### Sinusoidal and Star Targets

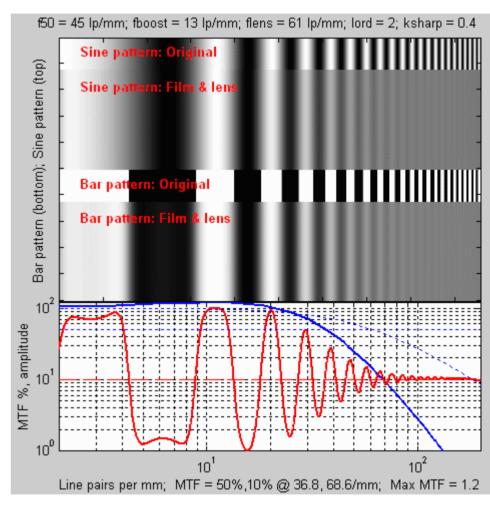




#### Modulation Transfer Function

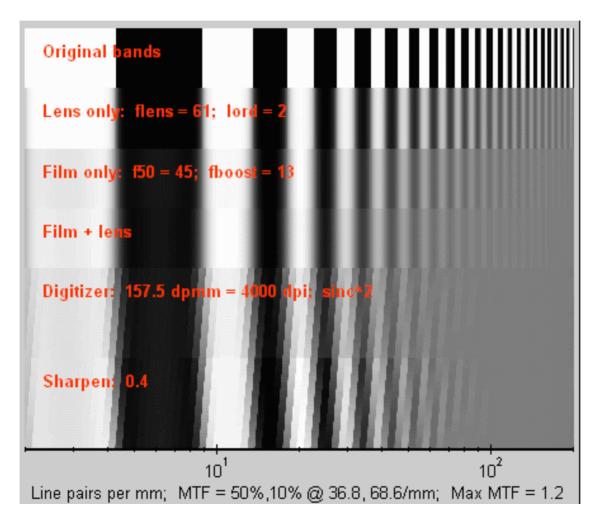
 Relation to pointspread function (PSF)





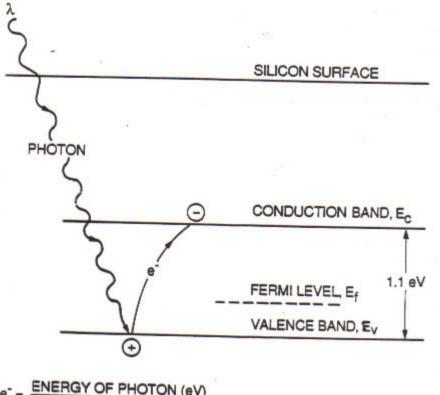
#### MTF

Effects of processing



## Step 2: Charge Generation

PHOTO-ELECTRIC EFFECT



Silicon

Similar physics for IR materials

## Detector Current Responsivity

5 = photocurrent
/incident power

 $S = QE \lambda qG/hc$ 

Rieke 2.13

```
where G = \tau / T \tau = carrier lifetime

T = transit time
```

(for photomultipliers, the photo-conductive gain G can be >>1!)

## Minimum Noise Equivalent Power

Detector internal Johnson noise limited:

$$\langle I_J \rangle^2 = 4kT \Delta f / R$$

NEP > 
$$I_J / S = [2hc/QE\lambda qG](kT/R)^{1/2} W/Hz^{1/2}$$

but most applications are not internal noise limited...

## Noise Equivalent Power

Include shot noise from input photons (so-called generation-recombination noise):

$$NEP_{G-R} > I_J / S = [2hc/\lambda](\phi/QE)^{1/2}$$
 W/Hz<sup>1/2</sup> sum:

$$NEP^2 = NEP_{G-R}^2 + NEP_J^2 + NEP_{1/f}^2$$

## Step 2: Charge Generation Photon Detection

For an electron to be excited from the conduction band to the valence band

$$h\nu > E_g$$

h = Planck constant (6.6310-34 Joule·sec) v = frequency of light (Hz) =  $\lambda/c$  $E_g$  = energy gap of material (electron-volts)



$$\lambda_c = 1.238 / E_g (eV)$$

Material Name	Symbol	$E_g \; (\mathrm{eV})$	$λ_c$ (μm)
Silicon	Si	1.12	1.1
Mer-Cad-Tel	HgCdTe	1.00 - 0.09	1.24 - 14
Indium Antimonide	InSb	0.23	5.9
Arsenic doped Silicon	Si:As	0.05	24

## Step 2: Charge Generation Photon Detection

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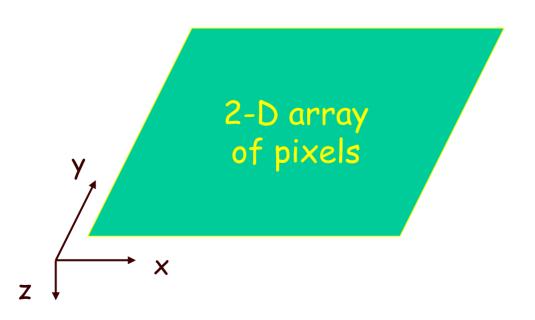


$$\lambda_c = 1.238 / E_g (eV)$$

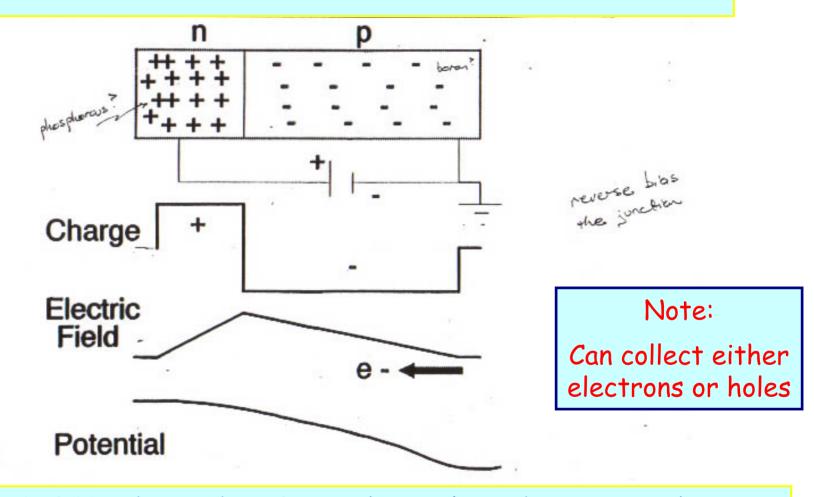
Material Name	Symbol	$E_g\ (\mathrm{eV})$	$λ_c$ (μm)	Operating Temp. (K)
Silicon	Si	1.12	1.1	163 - 300
Mer-Cad-Tel	HgCdTe	1.00 - 0.09	1.24 - 14	20 - 80
Indium Antimonide	InSb	0.23	5.9	30
Arsenic doped Silicon	Si:As	0.05	24	4

#### Step 3: Charge Collection

- Intensity image is generated by collecting photoelectrons generated in 3-D volume into 2-D array of pixels.
- Optical and IR focal plane arrays both collect charges via electric fields.
- In the z-direction, use an electric field to "sweep" charge toward pixel collection nodes.



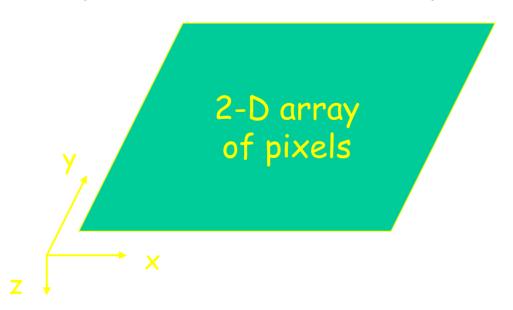
#### Photovoltaic Detector Potential Well



Silicon CCD & HgCdTe and InSb are photovoltaic detectors. They use a pn junction to generate E-field in the z-direction of each pixel. This electric field separates the electron-hole pairs generated by a photon.

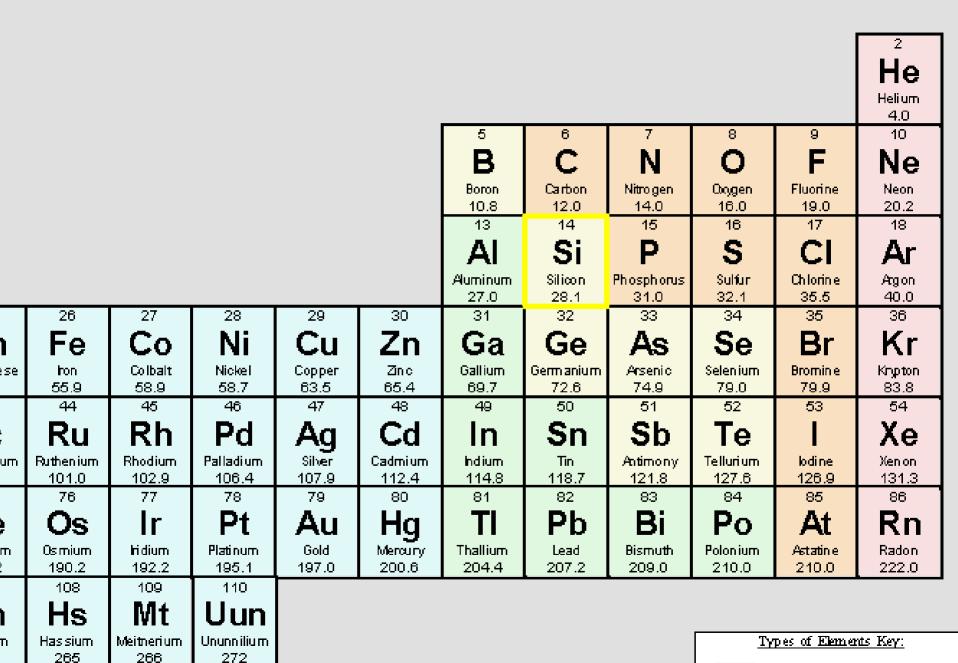
## Step 3: Charge Collection

- Optical and IR focal plane arrays are different for charge collection in the x and y dimensions.
- IR collect charge at each pixel and have amplifiers and readout multiplexer
- CCD collect charge in array of pixels. At end of frame, move charge to edge of array where one (or more) amplifier (s) read out the pixels.

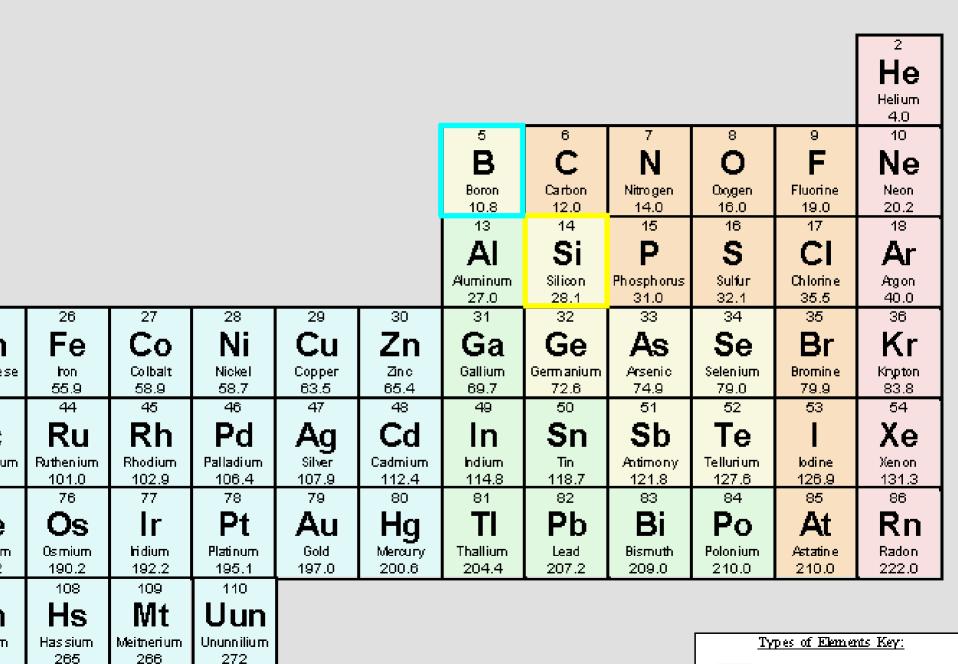


1 H Hydrogen 1.0																	Helium
3 <b>Li</b> Lithium	Be Beryllium											5 <b>B</b> Boron	Carbon	7 N Nitrogen	O Oxygen	9 <b>F</b> Fluorine	Ne Neon
6.9	9.0 12											10.8 13	12.0 14	14.0 15	16.0 16	19.0 17	20.2 18
Na	Mg											Αl	Si	P	S	CI	Ar
Sodium 23.0	Magnesium 9.0											Aluminum 27.0	Silicon 28.1	Phosphorus 31.0	Sulfur 32.1	Chlorine 35.5	Argon 40.0
19 <b>K</b>	Ca	21 <b>S</b> C	22 <b>Ti</b>	23 <b>V</b>	Cr	Mn 25	Fe	27 <b>C</b> 0	28 Ni	<sup>29</sup> Cu	<sup>∞</sup> Zn	<sup>∞</sup> Ga	<sup>∞</sup> Ge	As	Se	<sup>₃₅</sup> Br	<sup>36</sup> Kr
Potassium	Calcium	Scandium	Titanium	Vanadium	Chromium	Manganese	Iron	Colbalt	Nickel	Copper	Zinc	Gallium	Germanium	Arsenio	Selenium	Bromine	Krypton
39.1 37	40.2 38	45.0 39	47.9 40	50.9 41	52.0 42	54.9 43	55.9 44	58.9 45	58.7 46	63.5 47	65.4 48	69.7 49	72.6 50	74.9 51	79.0 52	79.9 53	83.8 54
Rb	Sr	Υ	Zr	Nb	Мо	Тс	Ru	Rh	Pd	Ag	Cd	In	Sn	Sb	Te	1	Xe
Rubidium 85.5	Strontium 87.6	Yitrium 88.9	⊠rconium 91.2	Niobium 92.9	Molybdenum 95.9	Technetium 99	Ruthenium 101.0	Rhodium 102.9	Palladium 106.4	Silver 107.9	Cadmium 112.4	hdium 114.8	Tin 118.7	Antimony 121.8	Tellurium 127.6	lodine 126.9	Xenon 131.3
55	56 <b>D</b> 0	57-71	Hf	Ta	74 <b>W</b>	Re	<sup>76</sup> Os	77   •	Pt	79 <b>A</b>	80 <b>U</b> ~	81 <b>TI</b>	Pb	₿i	Po	<sup>85</sup> <b>A</b> t	® Rn
Cs Caesium	Ba Barium		Hafrium	Tantalum	V V Tung <i>s</i> ten	Rhenium	Osmium	lr Iridium	Platinum	Au Gold	Hg Mercury	Thallium	Lead	Bismuth	Polonium	Astatine	Radon
132.9 87	137.4 88	89-103	178.5 104	181.0 105	183.9 106	186.2 107	190.2 108	192.2 109	195.1 110	197.0	200.6	204.4	207.2	209.0	210.0	210.0	222.0
Fr	Ra		Rf	Db	Sg	Bh	Hs	Mt	Uun								
Francium 223.0	Radium 226.0		Rutserfordium 261	Dubnium 262	Seaborgium 263	Bohrium 262	Hassium 265	Meitnerium 266	Ununnilium 272						TY	pes of Elemer	ts Key:
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57	58	59	60	61	62	63	64	65	66	67	80	69	70	71		c tinides	
Ľa	Сe	P̈́r	Ñd	Pm	Sm	вu	Ğd	Τ̈́b	Ďγ	Йо	Er	Τ̈́m	Ϋ́b	Lu	P	oor metak	
Lanthanum 138.9	Cerium 140.1	Praseodym Ium 140.9	Neodymium 144.2	Promethium 147.0	Samarium 150.4	Europium 152.0	Gadolinium 157.3	Terbium 158.9	Dysprosium 162.5	Holmium 164.9	Erbium 167.3	Thulium 168.9	Ytterbium 173.0	Lutetium 175.0	Se Se	emi-metak	
Ac	90 Th	91 Pa	92 <b>U</b>	93 <b>N</b> p	94 Pu	95 Am	°° Cm	97 Bk	es Cf	es Es	<sup>100</sup> Fm	Md	No	103   r	и	on-metak	
Atinium 132.9	Thorium 232.0	Protactinium 231.0	Uranium 238.0	Neptunium 237.0	Plutonium 242.0	Americium 243.0	Curium 247.0	Berkelium 247.0	Californium 251.0	En steinium 254.0	Fermium 253.0	Mendelevium 256.0	Nobelium 254.0	Lawrencium 257.0	и	oble gases	

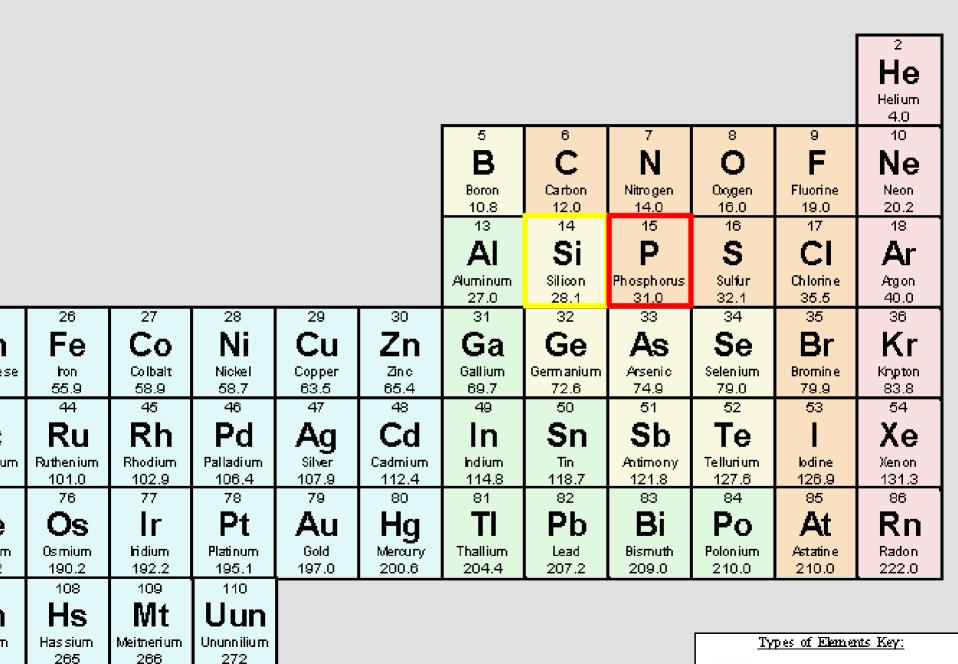
Hyd	1 H drogen 1.0																	He Helium 4.0				
1	3 Li thium	Be Beryllium											5 <b>B</b> Boron	C Carbon	7 <b>N</b> Nitrogen	8 Oxygen	9 <b>F</b> Fluorine	Ne Neon				
	6.9 11	9.0 12											10.8 13	12.0 14	14.0 15	16.0 16	19.0 17	20.2 18				
١N	Na	Mg											Al	Si	Р	S	CI	Ar				
	dium 23.0	Magnesium 9.0											Aluminum 27.0	Sili∞n 28.1	Phosphorus 31.0	Sulfur 32.1	Chlorine 35.5	Argon 40.0				
	19	20	21	22 <b>Ti</b>	23	24	25 D.C	26 <b>-</b>	27	28 N.I.	29	30	31	32	33 <b>A</b> =	34	35 <b>D</b>	36				
	K ssium	Ca	Sc Scandium	II II Titanium	V Vanadium	Cr	Mn Manganese	Fe	Co Colbalt	Ni Nickel	Cu Copper	Zn	Gallium	Ge Germanium	As Arsenio	Se Selenium	Br Bromine	Kr Kripton				
3	39.1 37	40.2 38	45.0 39	47.9 40	50.9 41	52.0 42	54.9 43	55.9 44	58.9 45	58.7 46	63.5 47	65.4 48	69.7 49	72.6 50	74.9 51	79.0 52	79.9 53	83.8 54				
	₹b	Sr	Ÿ	Žr	Nb	Mo	Tc	Ru	Rh	Pd	Äg	Cd	ln	Sn	Sb	Te	ï	Хe				
	bidium 35.5	Strontium 87.6	Yitrium 88.9	Zirconium 91.2	Niobium 92.9	Molybdenum 95.9	Technetium 99	Ruthenium 101.0	Rhodium 102.9	Palladium 106.4	Silver 107.9	Cadmium 112.4	hdium 114.8	Tin 118.7	Antimony 121.8	Tellurium 127.6	lodine 126.9	Xenon 131.3				
1	55	56	57-71	72	73	74	75	76	77	78	79	80	81	82	83	84	85	86				
	Cs	Ва		Hf	Ta	W	Re	Os	Ir	Pt	Au	Hg	TI	Pb	Bi	Po	At	Rn				
13	esium 32.9	Barium 137.4		Hafnium 178.5	Tantalum 181.0	Tungsten 183.9	Rhenium 186.2	0smium 190.2	hidium 192.2	Platinum 195.1	Gold 197.0	Mercury 200.6	Thallium 204.4	Lead 207.2	Bismuth 209.0	Polonium 210.0	Astatine 210.0	Radon 222.0				
	87 Fr	 Ra	89-103	Rf	Db	Sg	Bh	Hs	109 Mt	Uun												
_	n dium	Ra dium		Rutherfordism	Dubnium	Seaborgium	Bohrium	Hassium	Meitnerium	Ununnilium						Ty	pes of Elemen	ts Key:				
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13	38.9 89	140.1	140.9	144.2	147.0	150.4	152.0	157.3	158.9	162.5	164.9	167.3	168.9	173.0	175.0	5.0						
	%c	Th	Pa	U 92	<sup>sз</sup> <b>Q</b> И	Pu	Am	℃m	Bk	° Cf	es Es	Fm	Md	No	103 <b>Lr</b>	И	on-metak					
Acti	tinium 32.9	Thorium 232.0	Protactinium 231.0	Uranium 238.0	Neptunium 237.0	Plutonium 242.0	Americium 243.0	Curium 247.0	Berkelium 247.0	Californium 251.0	Ensteinium 254.0	Fermium 253.0	Mendelevium 256.0	Nobelium 254.0	Lawrencium 257.0	И	oble gases					



\_\_\_\_ Alkali metak

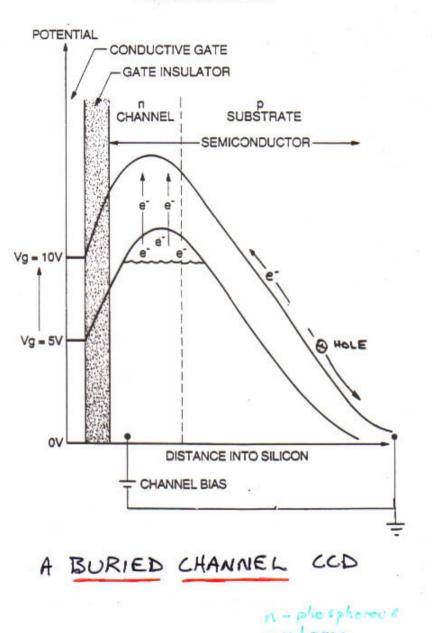


**Alkali metak** 



**Alkali metak** 

#### CCD POTENTIAL WELL



#### For silicon

n - region from phosphorous doping

p - region from boron doping

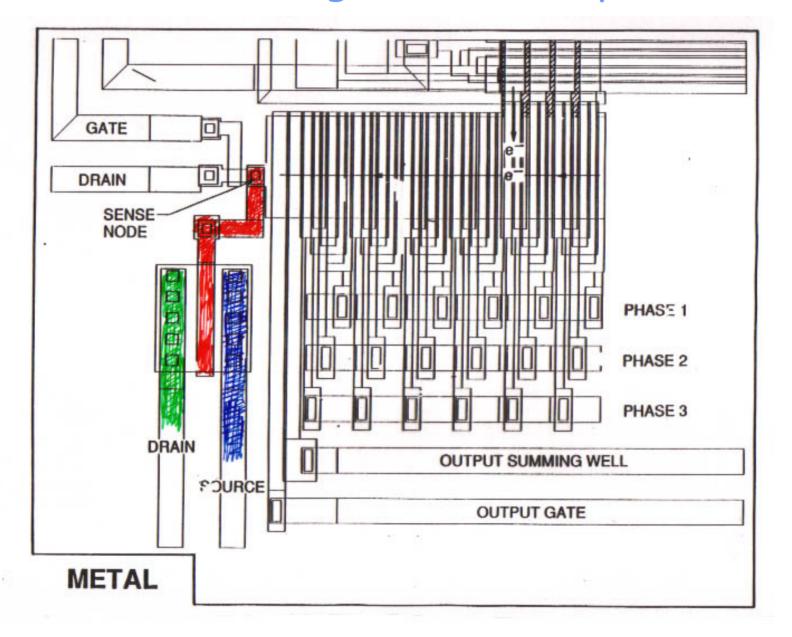
<u>n-channel CCD</u> collects electrons

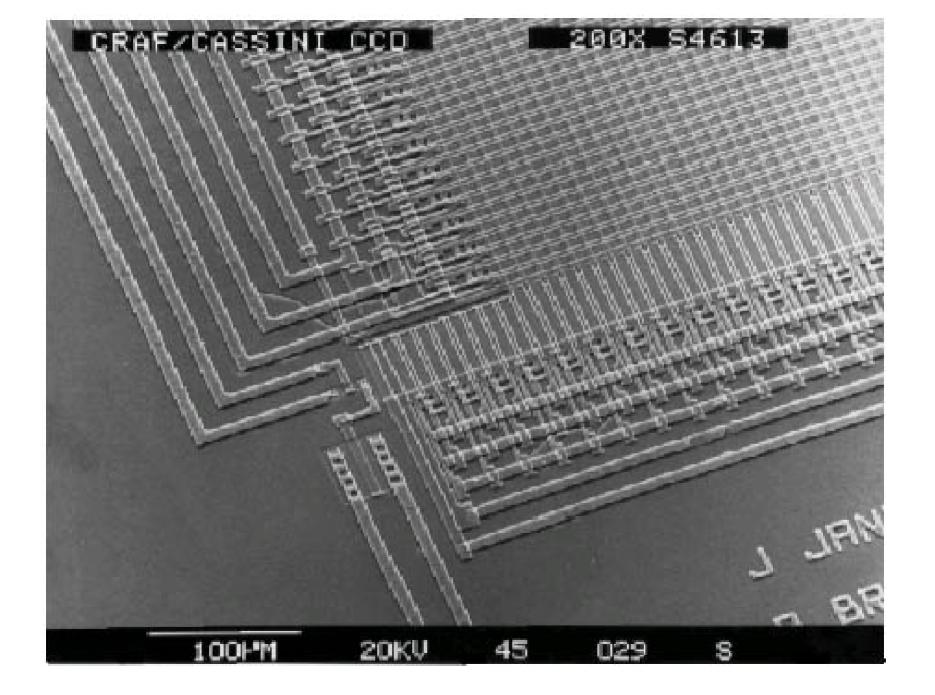
p-channel CCD collect holes

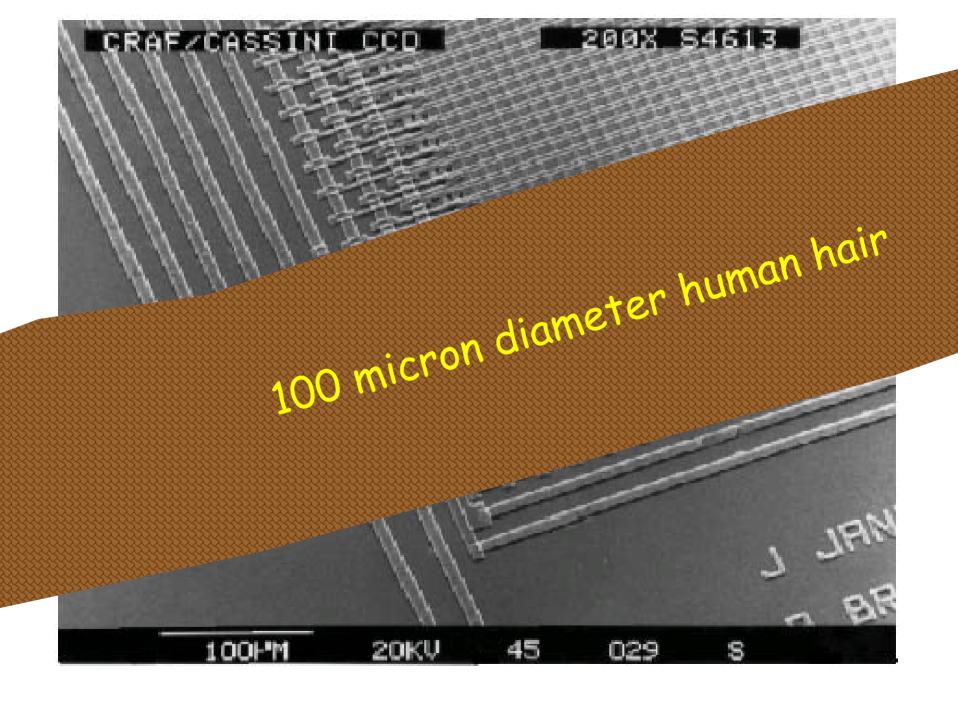
#### Steps 4 and 5: Charge transfer and amplification

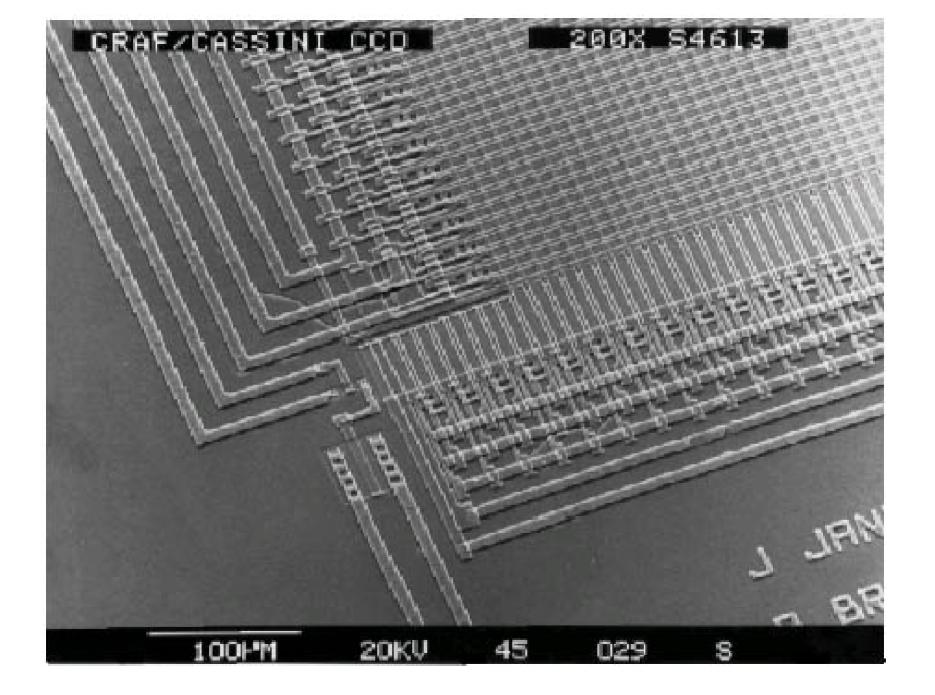
- Transfer different for CCDs and IR detectors (will cover next time).
- Both use MOSFETs (metal-oxidesemiconductor field effect transistors) to amplify the signal.

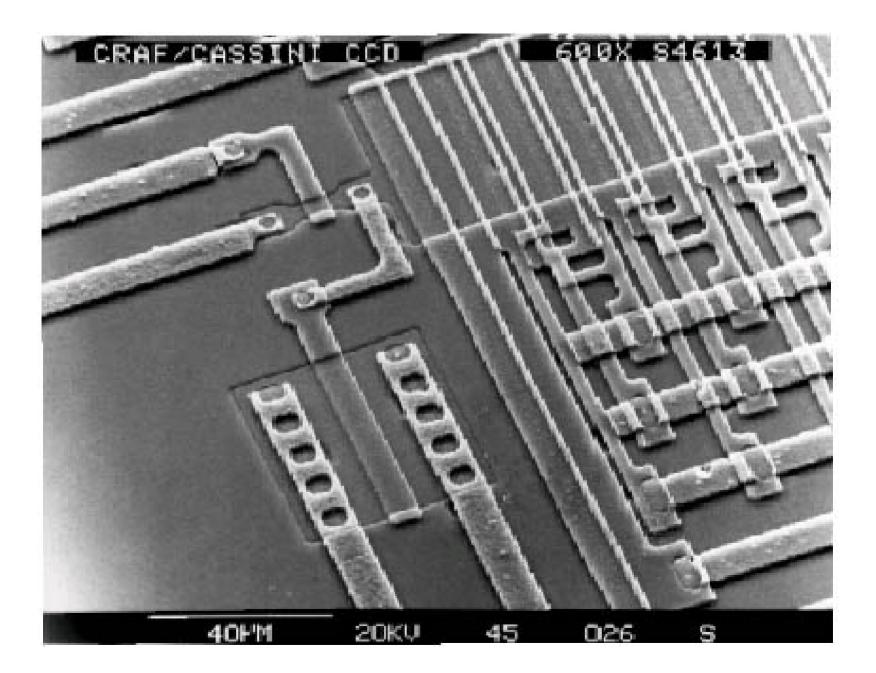
## CCD - Serial register and amplifier



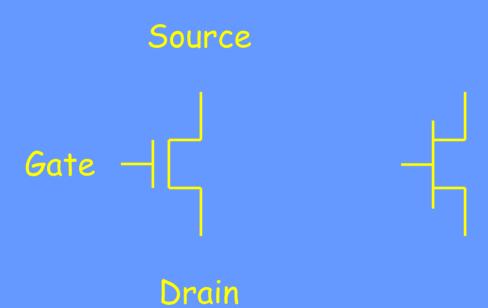


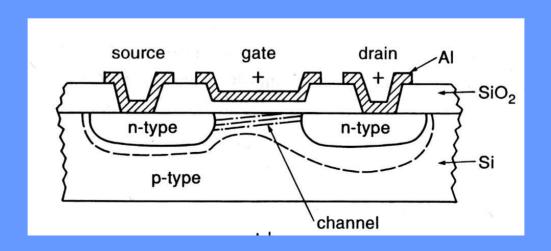




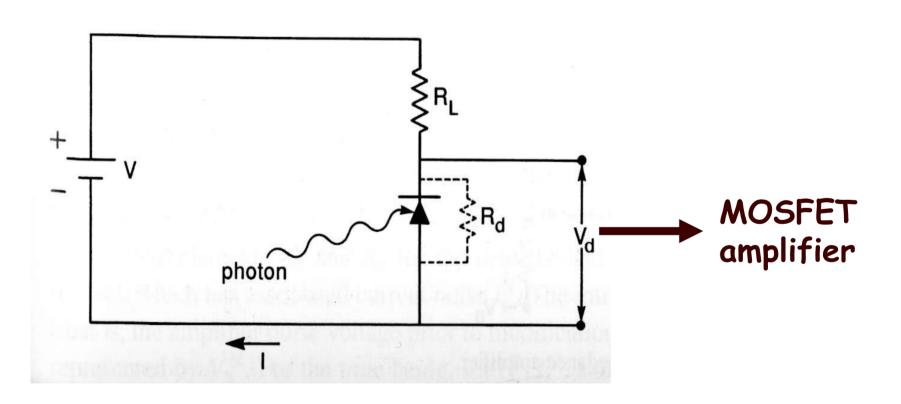


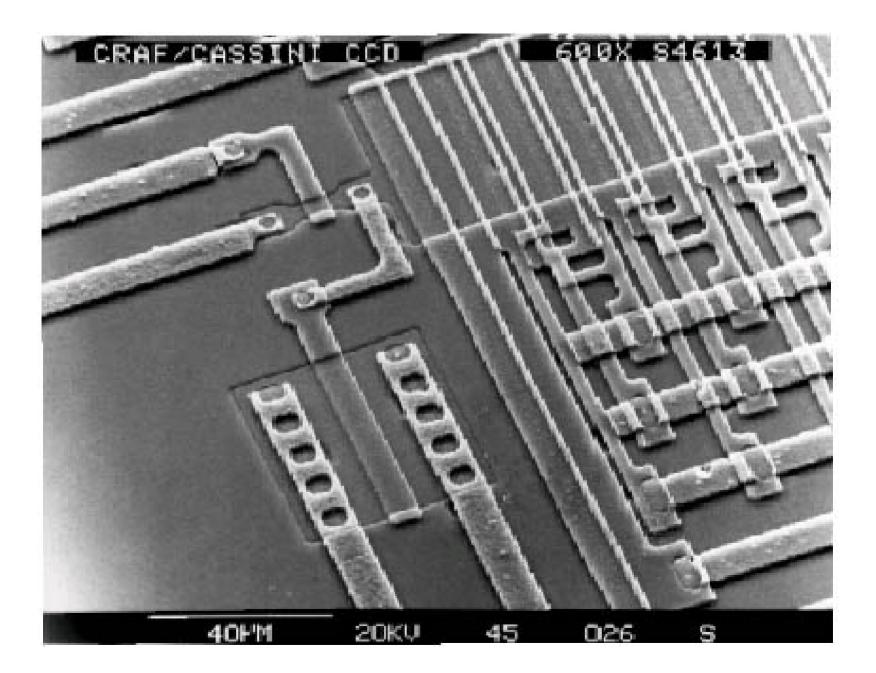
#### MOSFET





#### READOUT





## Amplifier Responsivity

Capacitance of MOSFET =  $10^{-13}$  F (100 fF) Responsivity of amplifier =  $1.6 \mu V / e^{-1}$ 

More recent amplifier designs have higher responsivity, 5 -  $10 \, \mu V/e^-$ , which give lower noise, but <u>less</u> dynamic range.